L Number	Hits	Search Text	DB	Time stamp
6	980	(plasma near etch\$3) and (copper near	USPAT;	2004/09/06 15:09
		plat\$3)	US-PGPUB;	2001, 05, 00 25.05
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	699	(plasma near etch\$3) and (copper near	USPAT	2004/09/06 15:09
		plat\$3)		
_	2	("20040063263").PN.	USPAT;	2004/09/06 11:15
	}		US-PGPUB;	
	İ		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1746	438/197	USPAT;	2004/09/02 10:46
			US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	45	438/197 and (backside or (back near side))	USPAT;	2004/09/02 11:23
			US-PGPUB;	
	1		EPO; JPO;	
	İ		DERWENT;	
	17100	(alooning gome wafor) and somiconductor	IBM_TDB USPAT:	2004/00/02 22 02
-	17120	(cleaning same wafer) and semiconductor		2004/09/02 11:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	2345	((cleaning same wafer) and semiconductor)	IBM_TDB USPAT;	2004/09/02 11:37
-	2345	and (plasma near etch\$3)	US-PGPUB;	2004/09/02 11:37
		and (prasma near ecchys)	EPO; JPO;	
			DERWENT;	
1			IBM TDB	
_	129	Toledo.xa.	USPAT;	2004/09/02 11:40
	127	10104017441	US-PGPUB;	2001/03/02 11:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	259	(wafer near clean\$3) and semiconductor and	USPAT;	2004/09/04 15:27
		(protective near (flim or layer))	US-PGPUB;	. ,
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	68476	Nakajima.in.	USPAT;	2004/09/04 15:29
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	225	Nebodine in and (IBM_TDB	0004/00/04 == ==
-	206	Nakajima.in. and (protective and semiconductor)	USPAT;	2004/09/04 15:30
		Semiconductor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	51	(Nakajima.in. and (protective and	USPAT;	2004/09/04 16:46
_	51	semiconductor)) and CVD	US-PGPUB;	2004/03/04 10:46
		Domitoliadolot / / dila CVD	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	o	"300.mm." and wafer and (clean\$3)	USPAT;	2004/09/04 16:47
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	-, -,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	"300.mm." near wafer	USPAT;	2004/09/04 16:47
			US-PGPUB;	
			EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	

-	0	"300.mm."	USPAT;	2004/09/04 16:47
	į		US-PGPUB;	
			EPO; JPO;	
	ļ		DERWENT;	
			IBM_TDB	
-	16321	"300" same wafer	USPAT;	2004/09/04 16:52
	1		US-PGPUB;	
İ			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6545	("300" same wafer) and clean\$3	USPAT;	2004/09/04 16:52
			US-PGPUB;	
			EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	
-	1494	(("300" same wafer) and clean\$3) and (plasma	USPAT;	2004/09/04 16:53
]	near etch\$3)	US-PGPUB;	!
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5834	l · ·	USPAT;	2004/09/04 16:48
İ		semiconductor	US-PGPUB;	
			EPO; JPO;	
		,	DERWENT;	
			IBM_TDB	
-	1390	((("300" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
	1	(plasma near etch\$3)) and semiconductor	US-PGPUB;	
	ļ		EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	645	(((("300" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
		(plasma near etch\$3)) and semiconductor) and	US-PGPUB;	
		(copper or Cu)	EPO; JPO;	ļ
			DERWENT;	
		((((())))	IBM_TDB	
-	39	((((("300" same wafer) and clean\$3) and	USPAT;	2004/09/04 17:10
		(plasma near etch\$3)) and semiconductor) and	US-PGPUB;	
		(copper or Cu)) and STI	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2722	"300 mm" same wafer	USPAT;	2004/09/04 16:52
			US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
		("000 "	IBM_TDB	0004/00/04 15 50
-	1456	("300 mm" same wafer) and clean\$3	USPAT;	2004/09/04 16:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1_	335	(("300 mm" same water) and cleares) and	IBM_TDB USPAT;	2004/09/04 16:53
1 -	335	, , , , , , , , , , , , , , , , , , , ,		2004/03/04 16:53
		(plasma near etch\$3)	US-PGPUB; EPO; JPO;	
			DERWENT;	
}			IBM TDB	
_	330	((("300 mm" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
_	330	(plasma near etch\$3)) and semiconductor	US-PGPUB;	2004/03/04 TO:33
		(probling hear econds)) and bellitconductor	EPO; JPO;	
			DERWENT;	
-			IBM TDB	
1_	132	(((("300 mm" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
1	132	(plasma near etch\$3)) and semiconductor) and	US-PGPUB;	
}		(copper or Cu)	EPO; JPO;	
		(55,502 55 56,	DERWENT;	
			IBM TDB	
1 -	10	((((("300 mm" same wafer) and clean\$3) and	USPAT;	2004/09/06 15:08
		(plasma near etch\$3)) and semiconductor) and	US-PGPUB;	
		(copper or Cu)) and STI	EPO; JPO;	
		Copper or only same was	DERWENT;	
			IBM TDB	
L	1	L		I

-	13	(backside near polish\$3) same (mirror) and	USPAT;	2004/09/04 17:15
		semiconductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	235	Maydan.in.	USPAT;	2004/09/04 17:15
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	333	Denning.in.	USPAT;	2004/09/06 11:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	163	Denning.in.	USPAT	2004/09/06 11:37
-	22	Kraft.in. and nitride	USPAT	2004/09/06 11:39
_	6688	copper near plating	USPAT	2004/09/06 11:40
-	10	(copper near plating) and STI	USPAT	2004/09/06 11:40